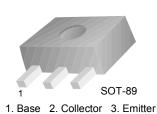
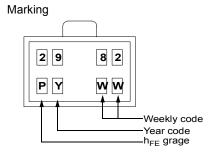


# **KSC2982 NPN Epitaxial Silicon Transistor**

### Strobe Flash & Medium Power Amplifier

- Excellent h<sub>FE</sub> Linearity : h<sub>FE1</sub>=140 ~ 600
- Low Collector-Emitter Saturation Voltage : V<sub>CE</sub>(sat)=0.5V
- Collector Dissipation : P<sub>C</sub>=1~2W in Mounted on Ceramic Board





### Absolute Maximum Ratings T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	30	V
V <sub>CES</sub>	Collector-Emitter Voltage	30	V
V <sub>CEO</sub>	Collector-Emitter Voltage	10	V
V <sub>EBO</sub>	Emitter Base Voltage	6	V
I <sub>C</sub>	Collector Current (DC)	2	Α
I <sub>CP</sub>	Collector Current (Pulse) *	4	А
I <sub>B</sub>	Base Current (DC)	0.4	А
I <sub>BP</sub>	Base Current (Pulse) *	0.8	А
P <sub>C</sub> P <sub>C</sub> *	Collector Power Dissipation	500 1,000	mW mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

<sup>\*</sup> PW  $\leq$  10ms, Duty Cycle  $\leq$  30%

Mounted on Ceramic Board (250mm<sup>2</sup> x 0.8mm)

# Electrical Characteristics T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0	10			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA, I <sub>C</sub> = 0	6			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 30V, I_{E} = 0$			100	nA
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>BE</sub> = 6V, I <sub>C</sub> = 0			100	nA
h <sub>FE1</sub> h <sub>FE2</sub>	DC Current Gain	$V_{CE} = 1V, I_{C} = 0.5A$ $V_{CE} = 1V, I_{C} = 2A$	140 70	140	600	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A, I <sub>B</sub> = 50mA		0.2	0.5	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> = 1V, I <sub>C</sub> = 2A		0.86	1.5	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = 1V, I <sub>C</sub> = 2A		150		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MHz		27		pF

# **h**<sub>FE</sub> Classification

	Classification	Α	В	С	D
Ī	h <sub>FE1</sub>	140 ~ 240	200 ~ 330	300 ~ 450	420 ~ 600

# **Package Marking and Ordering Information**

<b>Device Marking</b>	Device	Package	Reel Size	Tape Width	Quantity
2982	KSC2982	SOT-89	13"	-	4,000

### **Typical Performance Characteristics**

Figure 1. Static Characteristic

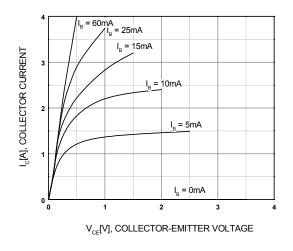


Figure 2. DC Current Gain

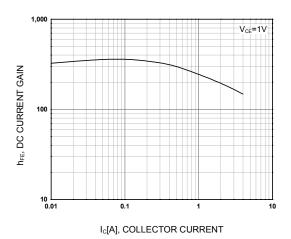
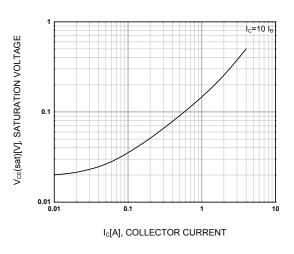


Figure 3. DCollector-Emitter Saturation Voltage Figure 4. Base-Emitter On Voltage



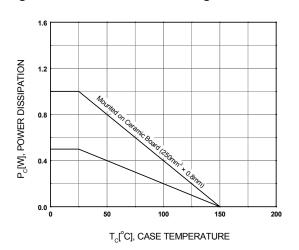


Figure 5. Safe Operating Area

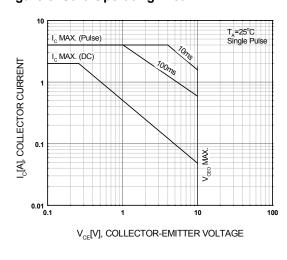
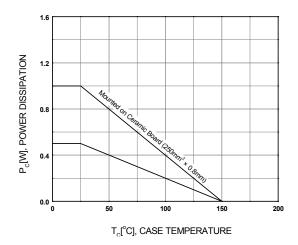


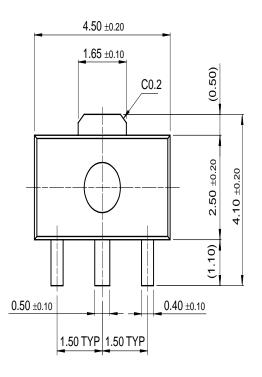
Figure 6. Power Derating

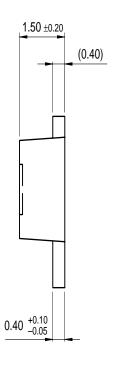


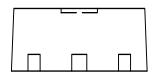
3 www.fairchildsemi.com

# **Mechanical Dimensions**

# **SOT-89**







Dimensions in Millimeters

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

SuperSOT™-6

### **PRODUCT STATUS DEFINITIONS**

#### **Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

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